

# Low-Voltage Sub-Ohm SPST/SPDT MICRO FOOT® Analog Switch

## DESCRIPTION

The DG3001/DG3002/DG3003 are monolithic CMOS analog switches designed for high performance switching of analog signals. The DG3001 and DG3002 are configured as SPST switches, and the DG3003 is an SPDT switch. Combining low power, high speed ( $t_{ON}$ : 47 ns,  $t_{OFF}$ : 40 ns), low on-resistance ( $r_{DS(on)}$ :  $0.4 \Omega$ ) and small physical size (MICRO FOOT, 6-bump), the DG3001/DG3002/DG3003 are ideal for portable and battery powered applications requiring high performance and efficient use of board space.

The DG3001/DG3002/DG3003 are built on Vishay Siliconix's low voltage J12 process. An epitaxial layer prevents latchup.

Each switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with the lead (Pb)-free device terminations. For MICRO FOOT analog switching products manufactured with tin/silver/copper (Sn/Ag/Cu) device terminations, the lead (Pb)-free "-E1" suffix is being used as a designator.

## FEATURES

- MICRO FOOT Chip Scale Package (1.0 x 1.5 mm)
- Low Voltage Operation (1.8 V to 5.5 V)
- Low On-Resistance -  $r_{DS(on)}$ :  $0.4 \Omega$
- Fast Switching -  $t_{ON}$ : 47 ns,  $t_{OFF}$ : 40 ns
- Low Power Consumption
- TTL/CMOS Compatible



**RoHS\***  
COMPLIANT

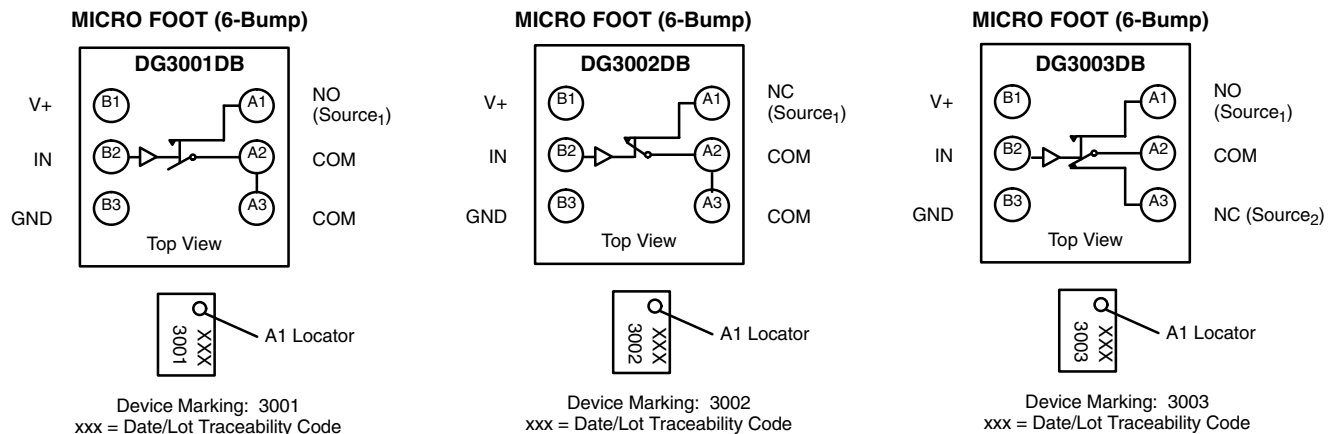
## BENEFITS

- Reduced Power Consumption
- Simple Logic Interface
- High Accuracy
- Reduce Board Space

## APPLICATIONS

- Cellular Phones
- Communication Systems
- Portable Test Equipment
- Battery Operated Systems
- PCM Cards
- PDA

## FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



## TRUTH TABLE

Logic	NC	NO
0	ON	OFF
1	OFF	ON

\* Pb containing terminations are not RoHS compliant, exemptions may apply

### ORDERING INFORMATION

Temp Range	Package	Part Number
- 40 to 85 °C	MICRO FOOT: 6/-Bump 3 x 2, 0.5-mm pitch, 165 µm nom. bump height (Eutectic, SnPb)	DG3001DB-T1
		DG3002DB-T1
		DG3003DB-T1
	MICRO FOOT: 6-Bump 3 x 2, 0.5-mm pitch, 238 µm nom. bump height (Lead (Pb)-free, Sn/Ag/Cu)	DG3001DB-T1-E1
		DG3002DB-T1-E1
		DG3003DB-T1-E1

### ABSOLUTE MAXIMUM RATINGS $T_A = 25\text{ °C}$ , unless otherwise noted

Parameter	Limit	Unit
Reference V+ to GND	- 0.3 to + 6	V
IN, COM, NC, NO <sup>a</sup>	- 0.3 to (V+ + 0.3 V)	
Continuous Current (NO, NC, COM)	± 250	mA
Peak Current (Pulsed at 1 ms, 10 % duty cycle)	± 400	
Storage Temperature	(D Suffix) - 65 to 150	°C
Package Reflow Conditions <sup>b</sup>	VPR (Eutectic) 215	
IR/Convection	(Eutectic) 220	
	(Lead (Pb)-free) 250	
Power Dissipation (Packages) <sup>c</sup>	6-Bump, 2 x 3 MICRO FOOT <sup>d</sup> 250	mW

Notes:

- Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- Refer to IPC/JEDEC (J-STD-020A)
- All bumps soldered to PC Board.
- Derate 3.1 mW/°C above 70 °C.



SPECIFICATIONS (V+ = 3.0 V)							
Parameter	Symbol	Test Conditions Otherwise Unless Specified V+ = 3 V, ± 10 %,VIN = 0.4 V or 2.0 V <sup>e</sup>	Temp <sup>a</sup>	Limits - 40 to 85 °C			Unit
				Min <sup>b</sup>	Typ <sup>c</sup>	Max <sup>b</sup>	
Analog Switch							
Analog Signal Range <sup>d</sup>	VNO, VNC, VCOM		Full	0		V+	V
On-Resistance <sup>d</sup>	rON	V+ = 2.7 V, VCOM = 1.5 V INO, INC = 10 mA	Room Full		0.4	0.7 0.8	Ω
rON Flatness <sup>d</sup>	rON Flatness	V+ = 2.7 V, VCOM = 0 to V+ INO, INC = 10 mA	Room		0.1	0.2	
rON Match <sup>d</sup>	ΔrON		Room		0.01	0.05	
Switch Off Leakage Current <sup>f</sup>	INO(off) INC(off)	V+ = 3.3 V, VNO, VNC = 0.3 V/3 V, VCOM = 3 V/0.3 V	Room Full	- 1 - 10		1 10	nA
	ICOM(off)		Room Full	- 1 - 10		1 10	
	Channel-On Leakage Current <sup>f</sup>		ICOM(on)	Room Full	- 1 - 10		
Digital Control							
Input High Voltage	VINH		Full	2			V
Input Low Voltage	VINL		Full			0.4	
Input Capacitance <sup>d</sup>	Cin		Full		5		pF
Input Current <sup>d</sup>	IINL or IINH	VIN = 0 or V+	Full	- 1		1	μA
Dynamic Characteristics							
Turn-On Time <sup>d</sup>	tON	VNO or VNC = 2.0 V, RL = 300 Ω, CL = 35 pF Figure 1 and 2	Room Full		47	71	ns
Turn-Off Time <sup>d</sup>	tOFF		Room Full		40	59	
Break-Before-Make Time <sup>d</sup>	td		Room	1	6		
Charge Injection <sup>d</sup>	QINJ	CL = 1 nF, VGEN = 0 V, RGEN = 0 Ω, Figure 3	Room		64		pC
Off-Isolation <sup>d</sup>	OIRR	RL = 50 Ω, CL = 5 pF, f = 100 kHz	Room		- 70		dB
Crosstalk <sup>d</sup>	XTALK		Room		- 70		
NO, NC Off Capacitance <sup>d</sup>	CNO(off) CNC(off)	VIN = 0 or V+, f = 1 MHz	Room		100		pF
Channel-On Capacitance <sup>d</sup>	CON		Room		340		
Power Supply							
Positive Supply Range	V+			2.7		3.3	V
Negative Supply Current	I+	VIN = 0 or V+			0.1	1.0	μA

## Notes:

a. Room = 25 °C, Full = as determined by the operating suffix.

b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

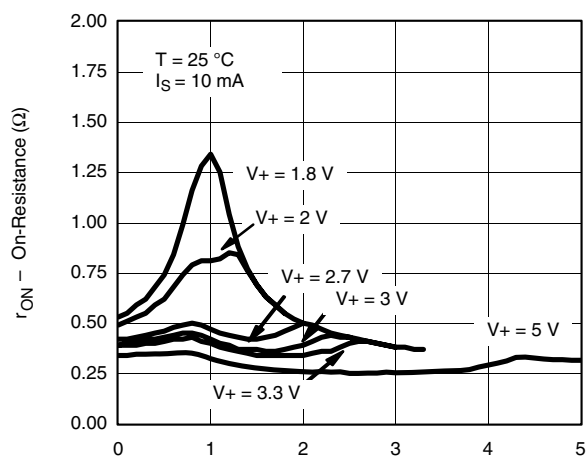
c. Typical values are for design aid only, not guaranteed nor subject to production testing.

d. Guarantee by design, nor subjected to production test.

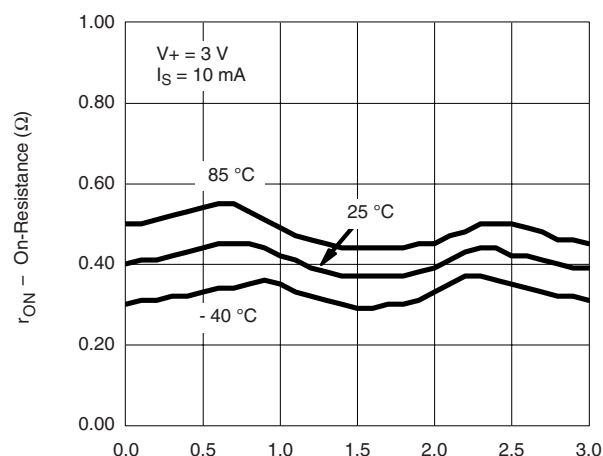
e. V<sub>IN</sub> = input voltage to perform proper function.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

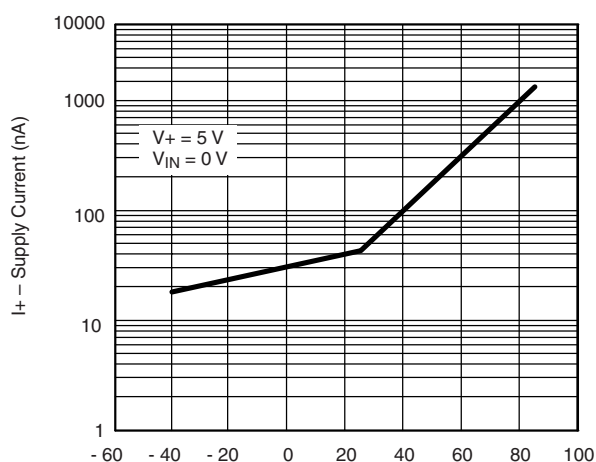
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



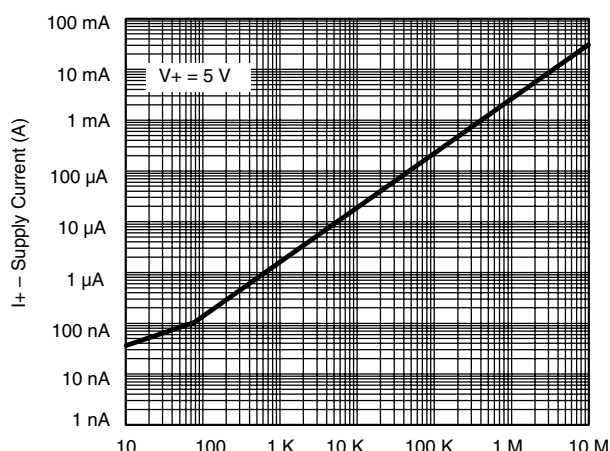
$r_{ON}$  vs.  $V_{COM}$  and Supply Voltage



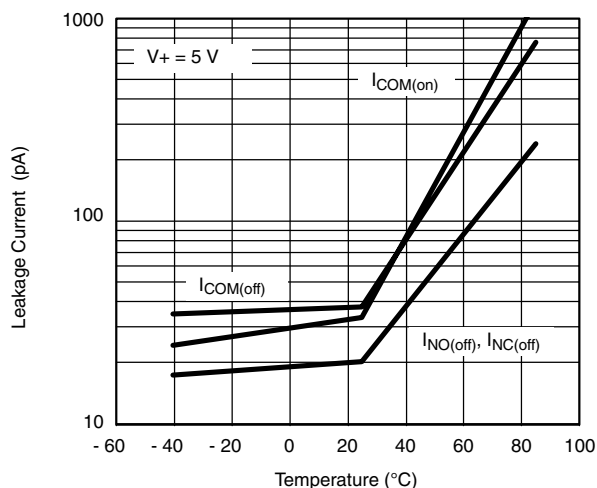
$r_{ON}$  vs. Analog Voltage and Temperature



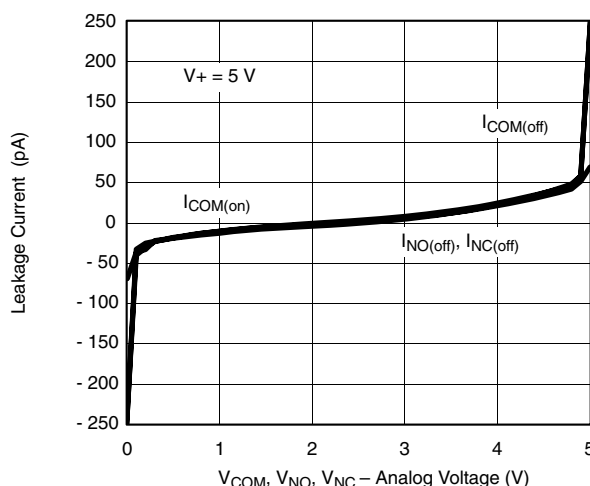
Supply Current vs. Temperature



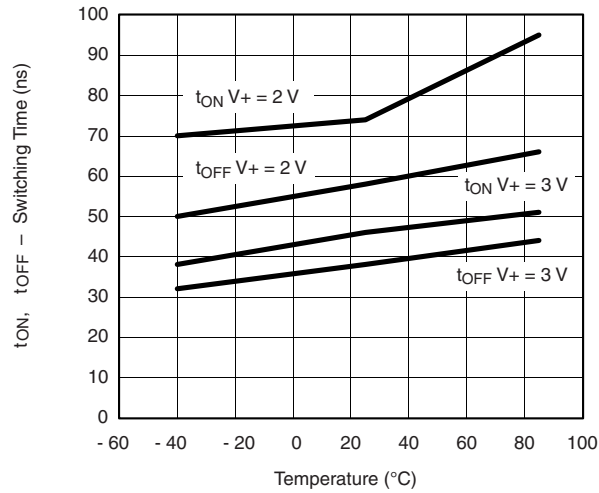
Supply Current vs. Input Switching Frequency



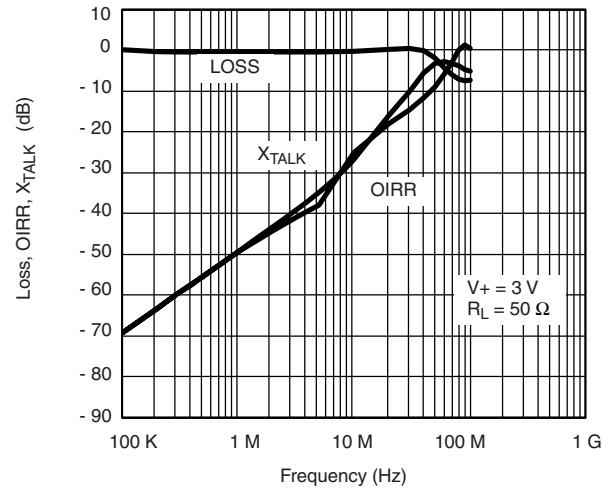
Leakage Current vs. Temperature



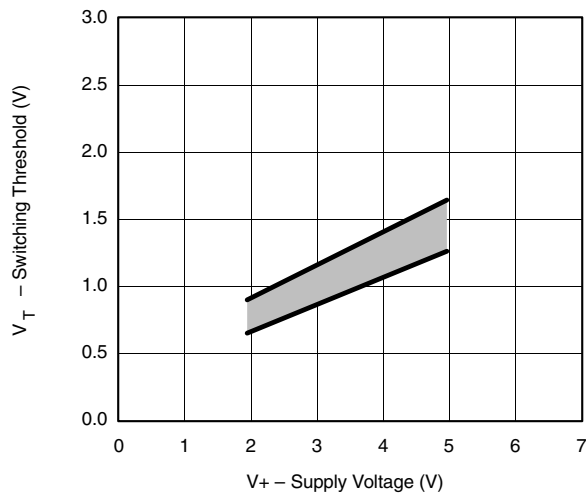
Leakage vs. Analog Voltage

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted


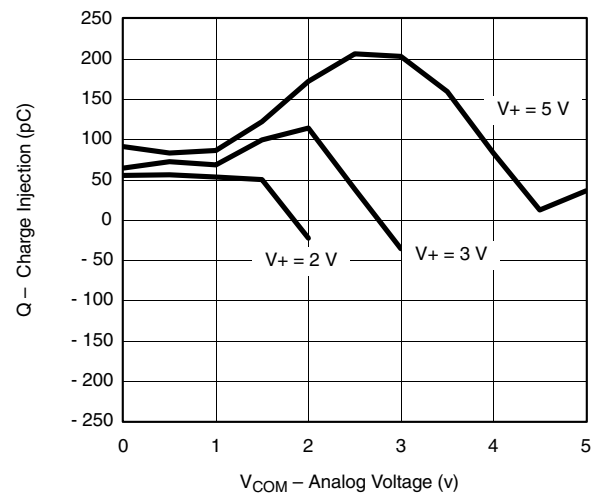
**Switching Time vs. Temperature and Supply Voltage**



**Insertion Loss, Off-Isolation, Crosstalk vs. Frequency**



**Switching Threshold vs. Supply Voltage**



**Charge Injection vs. Analog Voltage**

## TEST CIRCUITS

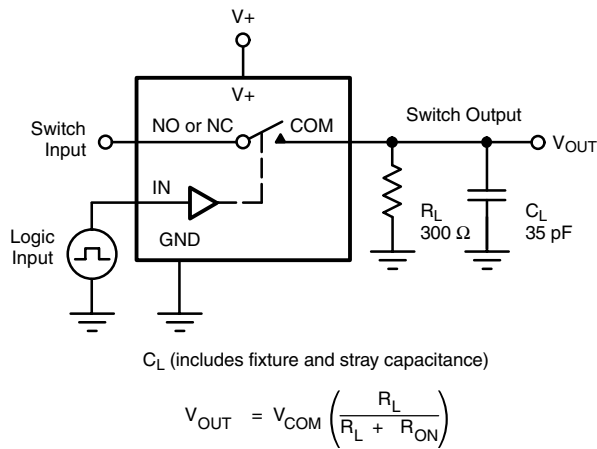
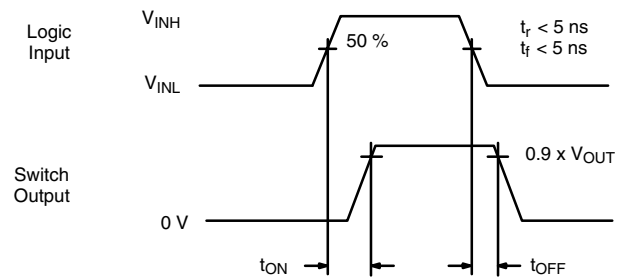


Figure 1. Switching Time



Logic "1" = Switch On  
Logic input waveforms inverted for switches that have the opposite logic sense.

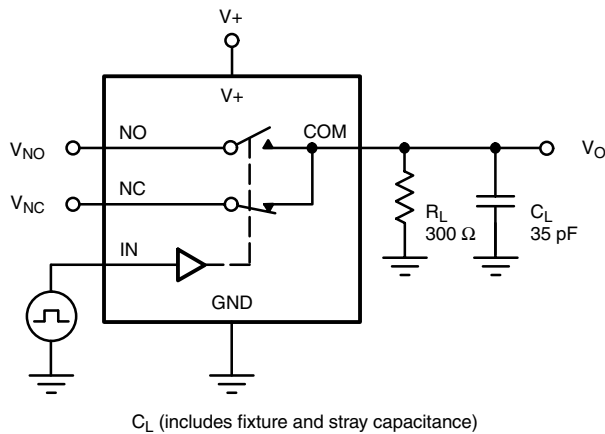


Figure 2. Break-Before-Make Interval

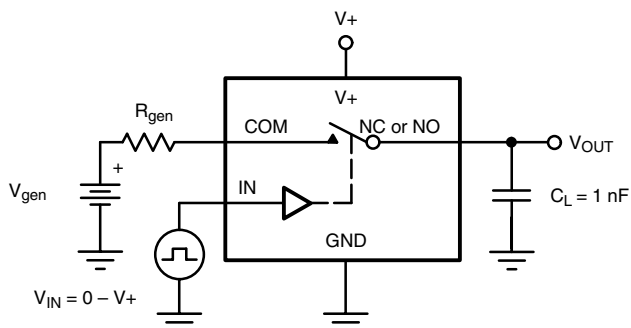
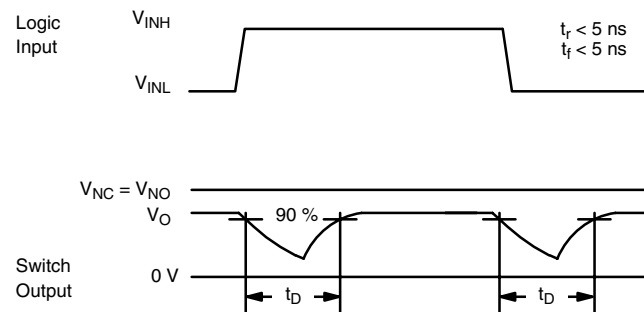
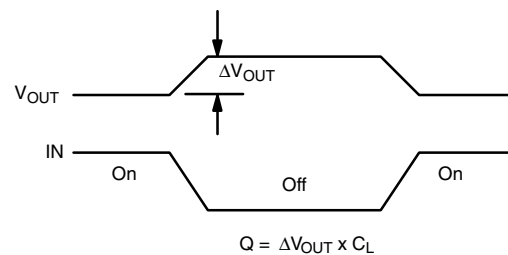
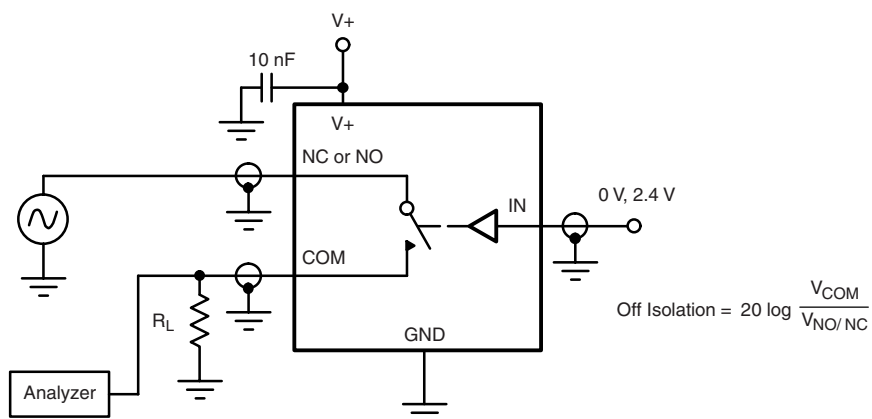
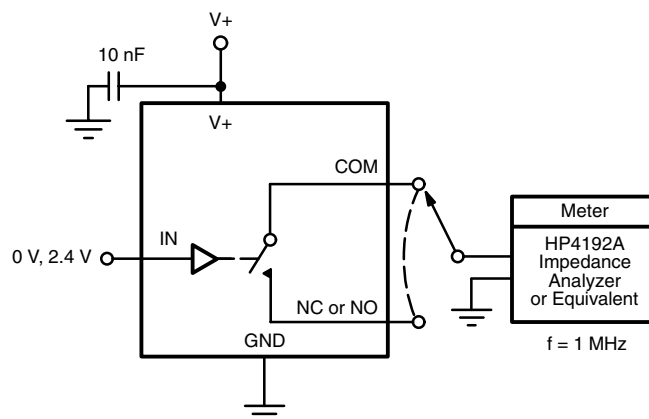


Figure 3. Charge Injection

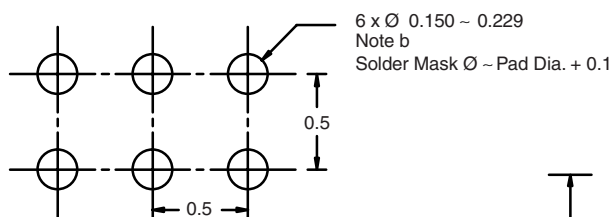


IN depends on switch configuration: input polarity determined by sense of switch.

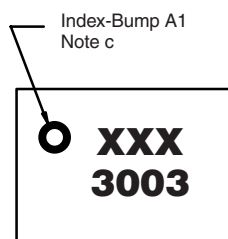
**TEST CIRCUITS**

**Figure 4. Off-Isolation**

**Figure 5. Channel Off/On Capacitance**

### PACKAGE OUTLINE

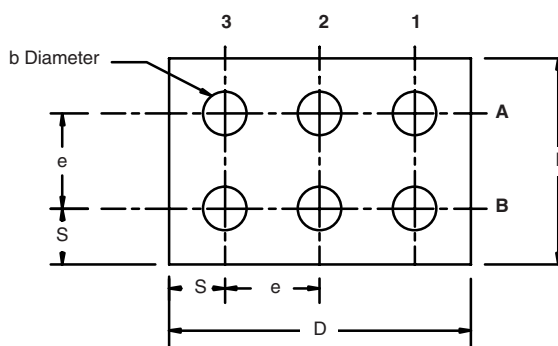
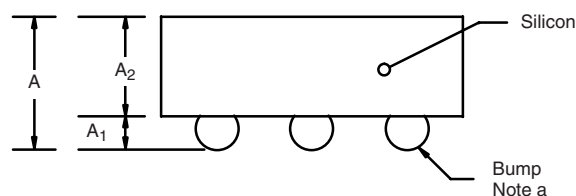
#### MICRO FOOT: 6-BUMP (3 x 2, 0.5 mm PITCH, 165 µm BUMP HEIGHT)



Recommended Land Pattern



Top Side (Die Back)



Notes (Unless Otherwise Specified):

- a. Bump is Eutectic 63/57 Sn/Pb or Lead (Pb)-free Sn/Ag/Cu.
- b. Non-solder mask defined copper landing pad.
- c. Laser Mark on silicon die back; no coating. Shown is not actual marking; sample only.

EUTECTIC (Sn/Pb)				
Dim	Millimeters <sup>a</sup>		Inches	
	Min	Max	Min	Max
A	0.610	0.685	0.0240	0.0270
A <sub>1</sub>	0.140	0.190	0.0055	0.0075
A <sub>2</sub>	0.470	0.495	0.0185	0.0195
b	0.180	0.250	0.0071	0.0098
D	1.490	1.515	0.0587	0.0596
E	0.990	1.015	0.0390	0.0400
e	0.5 BASIC		0.0197 BASIC	
S	0.245	0.258	0.0096	0.0101

Notes:

- a. Use millimeters as the primary measurement.

LEAD (Pb)-FREE (Sn/Ag/Cu)				
Dim	Millimeters <sup>a</sup>		Inches	
	Min	Max	Min	Max
A	0.688	0.753	0.0271	0.0296
A <sub>1</sub>	0.218	0.258	0.0086	0.0102
A <sub>2</sub>	0.470	0.495	0.0185	0.0195
b	0.306	0.346	0.0120	0.0136
D	1.490	1.515	0.0587	0.0596
E	0.990	1.015	0.0390	0.0400
e	0.5 BASIC		0.0197 BASIC	
S	0.245	0.258	0.0096	0.0102

Notes:

- a. Use millimeters as the primary measurement.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?72505>.





### Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.